

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07703

DT-33-11

2SC3346

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

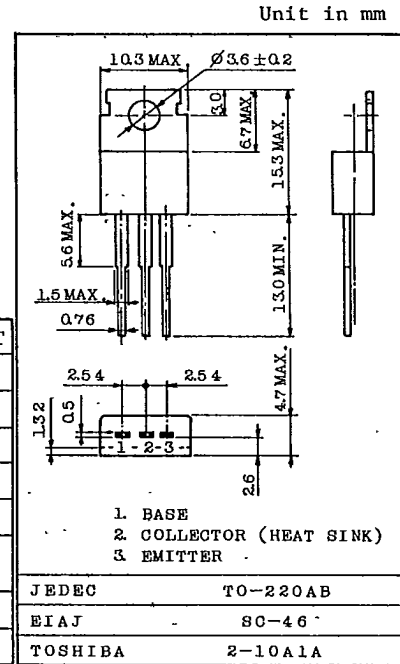
HIGH CURRENT SWITCHING APPLICATIONS.

FEATURES:

- Low Collector Saturation Voltage
: $V_{CE(sat)}=0.4V$ (Max.) (at $I_C=6A$)
- High Speed Switching Time : $t_{stg}=1.0\mu s$ (Typ.)
- Complementary to 2SA1329

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	12	A
Base Current	I_B	2	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	40	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=80V, I_E=0$	-	-	10	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=6V, I_C=0$	-	-	10	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C=50mA, I_B=0$	80	-	-	V
DC Current Gain		$h_{FE(1)}$ (Note)	$V_{CE}=1V, I_C=1A$	70	-	240	
		$h_{FE(2)}$	$V_{CE}=1V, I_C=6A$	40	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C=6A, I_B=0.3A$	-	0.2	0.4	V
	Base-Emitter	$V_{BE(sat)}$	$I_C=6A, I_B=0.3A$	-	0.9	1.2	
Transition Frequency		f_T	$V_{CE}=5V, I_C=1A$	-	80	-	MHz
Collector Output Capacitance		C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	220	-	pF
Switching Time	Turn-on Time	t_{on}		-	0.2	-	μs
	Storage Time	t_{stg}		-	1.0	-	
	Fall Time	t_f		-	0.2	-	

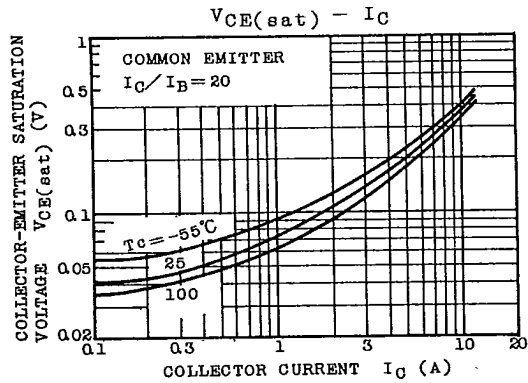
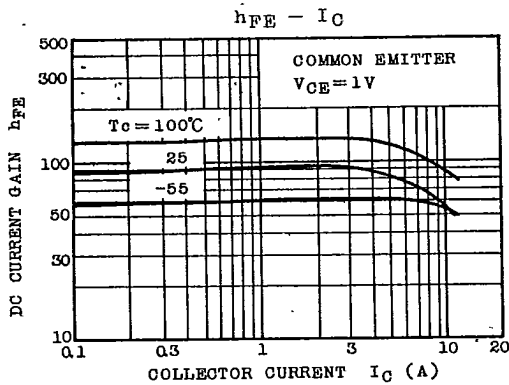
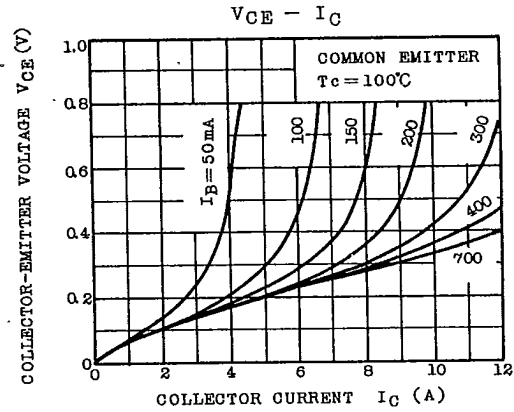
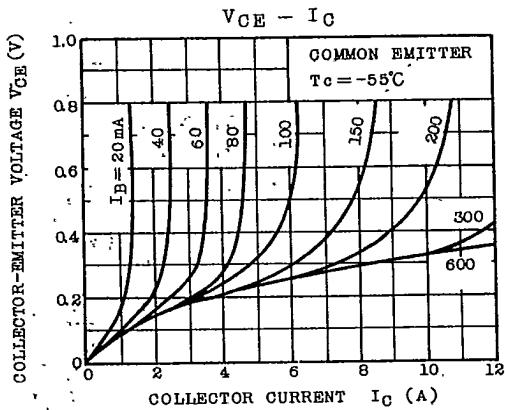
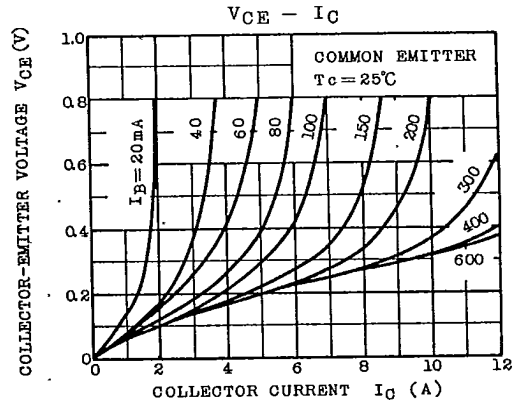
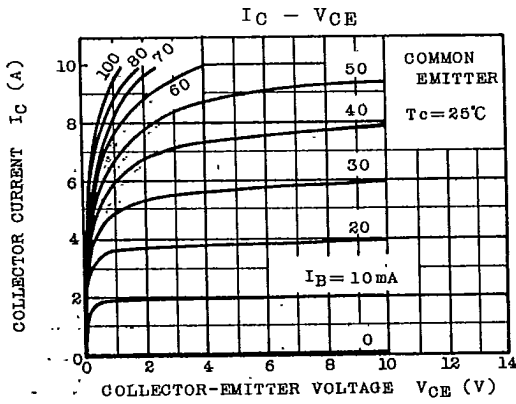
Note : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

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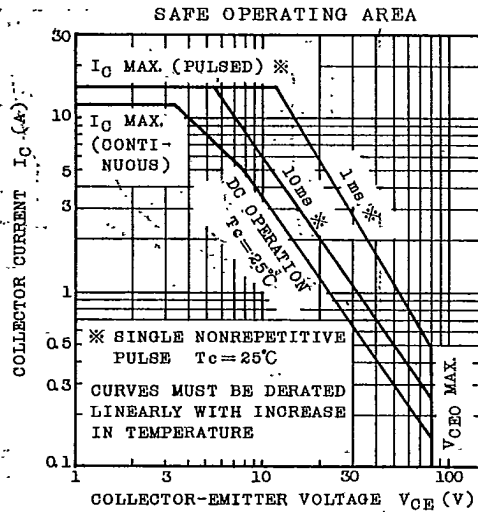
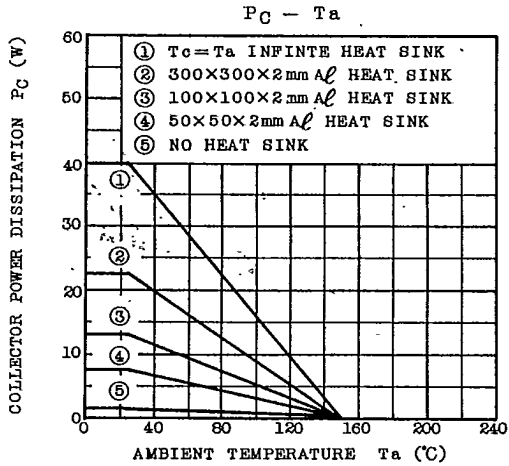
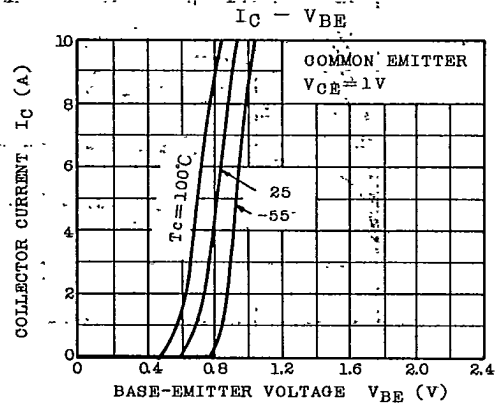
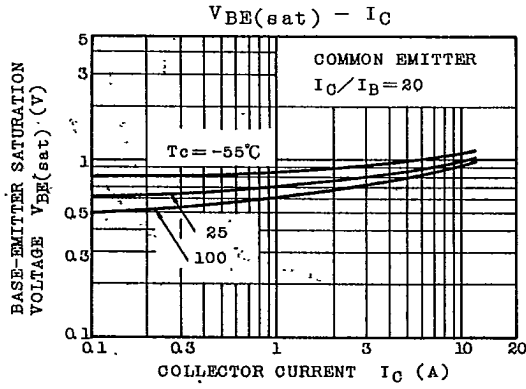
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